

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **KANO et al.**

Serial No.: **09/941,982**

Filed: **August 30, 2001**



Group Art Unit: **2812**

Examiner: **Mulpuri, Savitri**

P.T.O. Confirmation No.: 7536

For. **METHOD OF FORMING NITRIDE-BASED SEMICONDUCTOR LAYER, AND
METHOD OF MANUFACTURING NITRIDE-BASED SEMICONDUCTOR
DEVICE**

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Date: October 9, 2003

Sir:

Prior to continued examination, please amend the above-identified application as follows: